



SiC SCHOTTKY DIODE TYPE 2×200A

Preliminary

Features

- High surge current capable
- Zero reverse recovery current
- High bandwidth
- Temperature Independent Switching Behavior
- VDC 600 V
- I_F ($T_C < 135^\circ\text{C}$) 2×200 A

Benefits

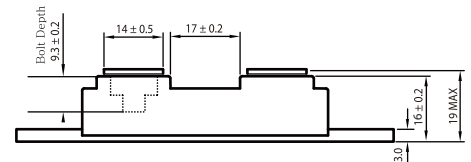
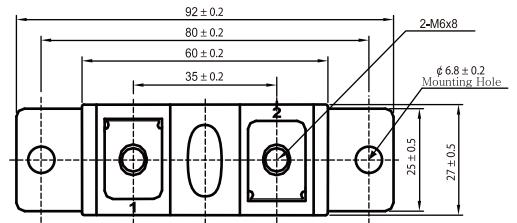
- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices without thermal runaway

Applications

- Motor drives
- Switch mode power supplies
- Ev chargers
- Solar inverters
- Welding equipment
- Power factor correction
- Diode snubber
- Automotive
- induction heating



Dimensions in mm (1 mm = 0.0394")



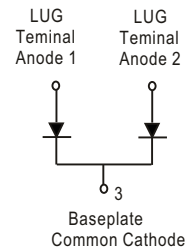
Maximum Ratings

Operating Junction Temperature : - 55 °C to +175 °C

Storage Temperature : -55 °C to +175 °C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
DACSB40060CT	600V	600V

Maximum Rating	Symbol	Conditions	Value	Unit
Continuous forward current (per leg)	I_F	$T_C = 135^\circ\text{C}$	200	A
Surge non-repetitive forward current sine halfwave (per leg)	I_{FSM}	$T_C = 25^\circ\text{C}$, $t_p = 8.3\text{ ms}$	1400	
		$T_C = 150^\circ\text{C}$, $t_p = 8.3\text{ ms}$	875	
Non-repetitive peak forward current (per leg)	$I_{F,max}$	$T_C = 25^\circ\text{C}$, $t_p = 10\ \mu\text{s}$	5600	
		$T_C = 150^\circ\text{C}$, $t_p = 10\ \mu\text{s}$	3500	
Repetitive peak reverse voltage	V_{RRM}	$T_j = 25^\circ\text{C}$	600	V
Mounting torque		M6 Screw	3~4.7	N-m





Electrical Characteristics, at Tj=25 °C, unless otherwise specified. (per leg)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	V _{DC}		600	-	-	V
Diode forward voltage	V _F	I _F =200A, T _J =25 °C	-	1.45	1.65	
		I _F =200A, T _J =175 °C	-	1.70	2.00	
Reverse current	I _R	V _R =600V, T _J =25 °C	-	30	200	μA
		V _R =600V, T _J =175 °C	-	200	1,000	

AC Characteristics (per leg)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Total capacitive charge	Q _{rr}	V _R =400V, T _J =25 °C	-	698	-	nC
Total capacitance	C	V _R =0V, f=1 MHz T _J =25 °C	-	12,580	-	pF
		V _R =200V, f=1 MHz T _J =25 °C	-	1,250	-	
		V _R =400V, f=1 MHz T _J =25 °C	-	1,170	-	

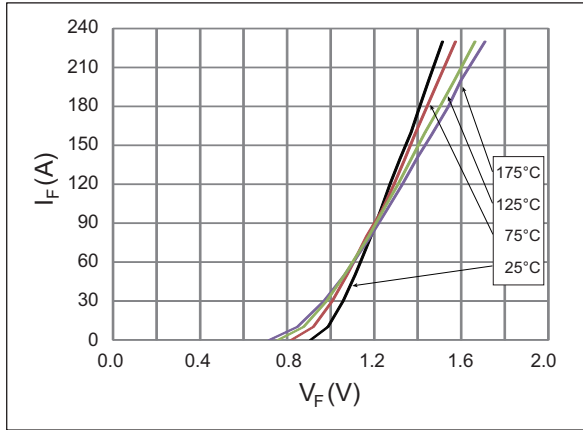
Thermal Characteristics (per leg)

Static Characteristics	Symbol	Values	Unit
		typ.	
Thermal resistance from junction to case	R _{θJC}	0.07	°C/W

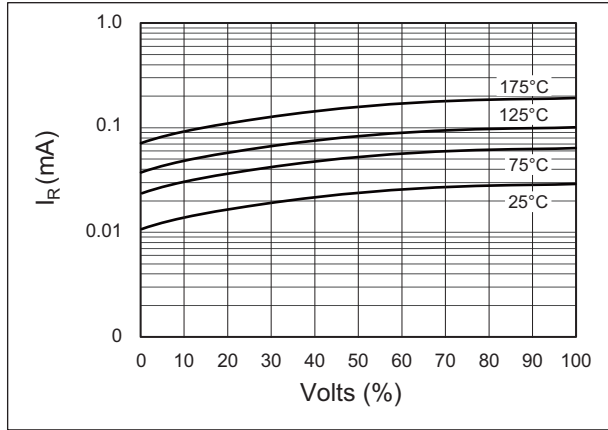


Typical Performance

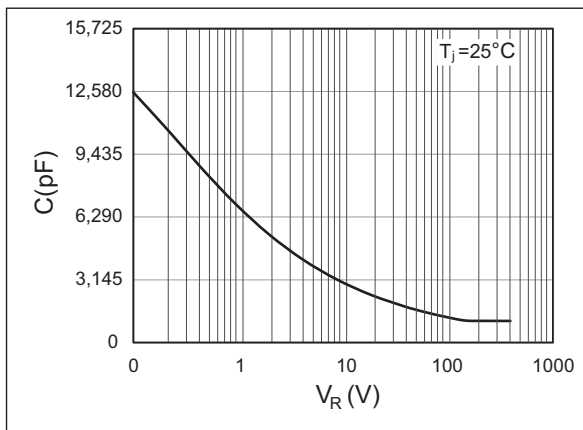
Forward Characteristics (parameterized on T_j)



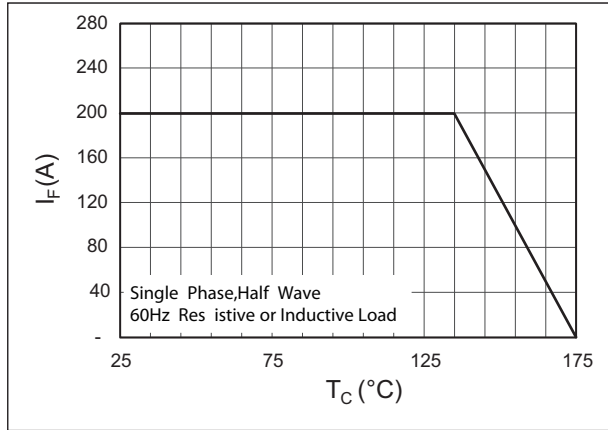
Reverse Characteristics (parameterized on T_j)



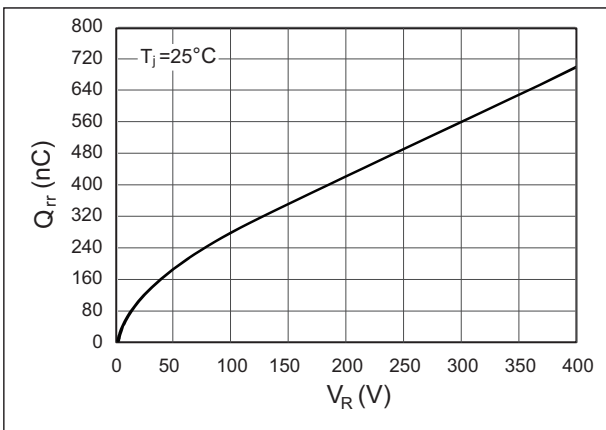
Capacitance



Current Derating



Recovery Charge



Forward Surge Current

